Ordering number : ENA0413

SANYO Semiconductors
DATA SHEET

2SC6098 — NPN Epitaxial Planar Silicon Transistor
High-Voltage Switching Applications

Applications

- DC / DC converter, relay drivers, lamp drivers, motor drivers, inverter.

Features

- Adoption of FBET, MBIT process.
- High current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		120	V
Collector-to-Emitter Voltage	V_{CES}		120	V
Collector-to-Emitter Voltage	V_{CEO}		80	V
Emitter-to-Base Voltage	V_{EBO}		6.5	V
Collector Current	I_C		2.5	A
Collector Current (Pulse)	I_{CP}		4	A
Base Current	I_B		500	mA
Collector Dissipation	P_C		0.8	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=70V, I_E=0A			1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0A			1	μA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=100mA	300		600	

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SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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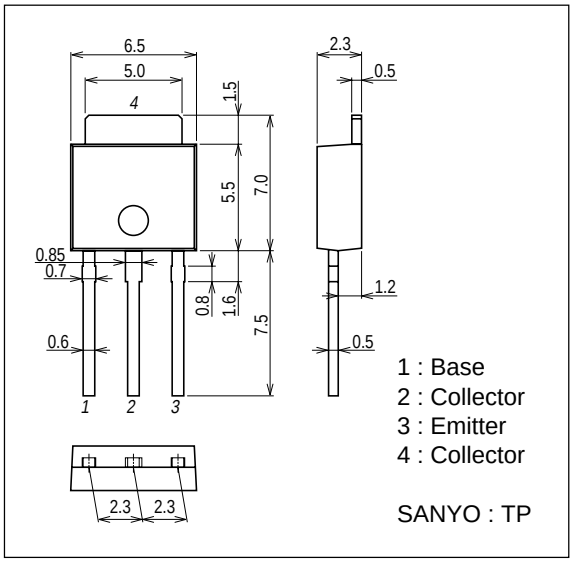
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=500mA		350		MHz
Output Capacitance	Cob	V_{CB}=10V, f=1MHz		14		pF
Collector-to-Emitter Saturation Voltage	$V_{CE}(sat)1$	I_C=1A, I_B=50mA		110	165	mV
	$V_{CE}(sat)2$	I_C=1A, I_B=100mA		100	150	mV
Base-to-Emitter Saturation Voltage	$V_{BE}(sat)$	I_C=1A, I_B=100mA		0.9	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0A	120			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=100μA, R_{BE}=0Ω	120			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	80			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0A	6.5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		40		ns
Storage Time	t_{stg}	See specified Test Circuit.		920		ns
Fall Time	t_f	See specified Test Circuit.		32		ns

Package Dimensions

unit : mm

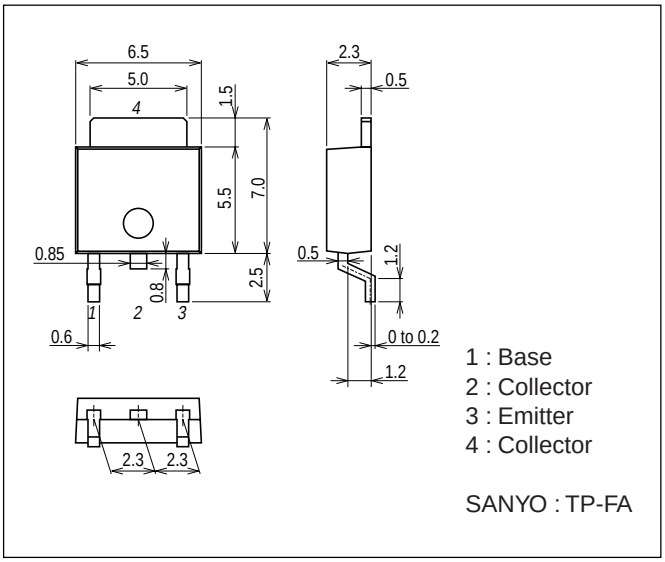
7518-003



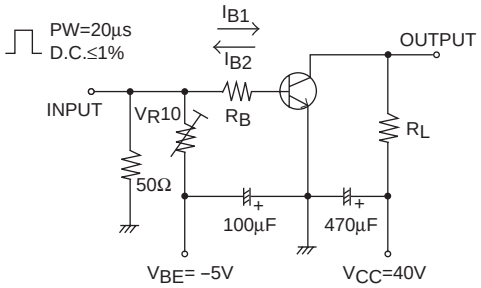
Package Dimensions

unit : mm

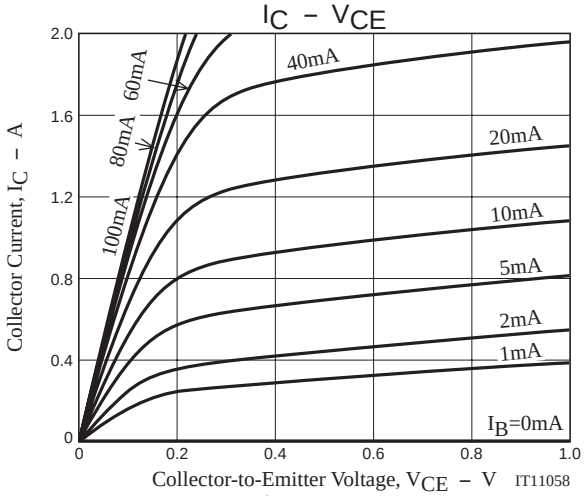
7003-003

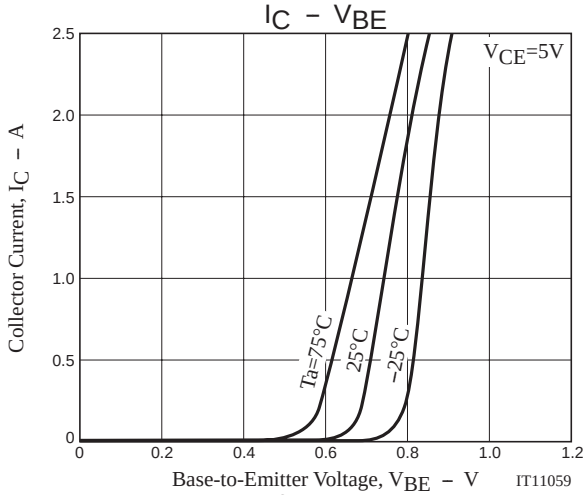


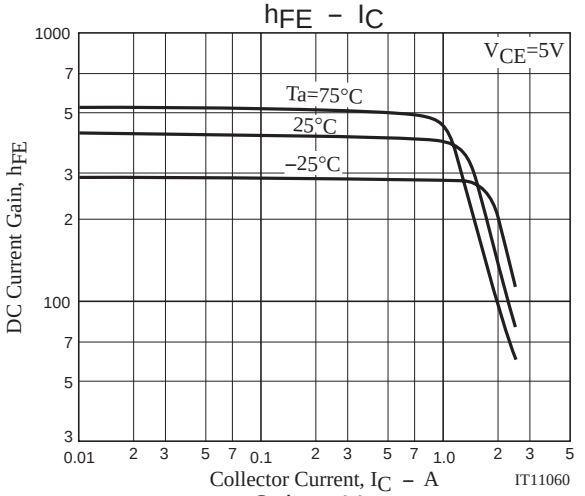
Switching Time Test Circuit

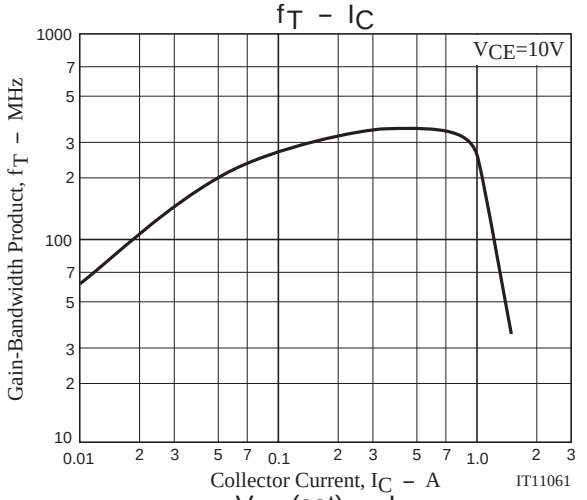


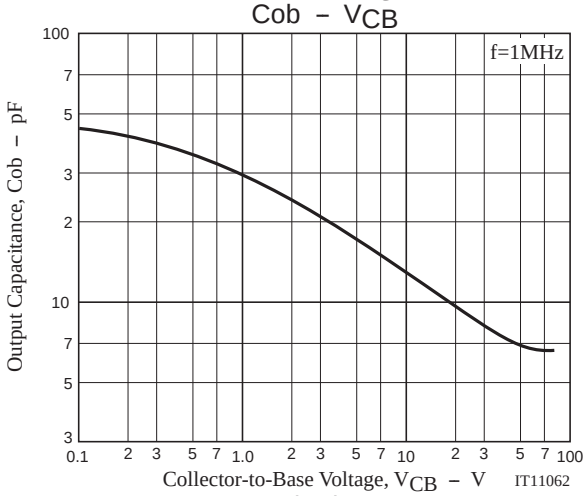
$10I_{B1}= -10I_{B2}=I_C=0.5A$

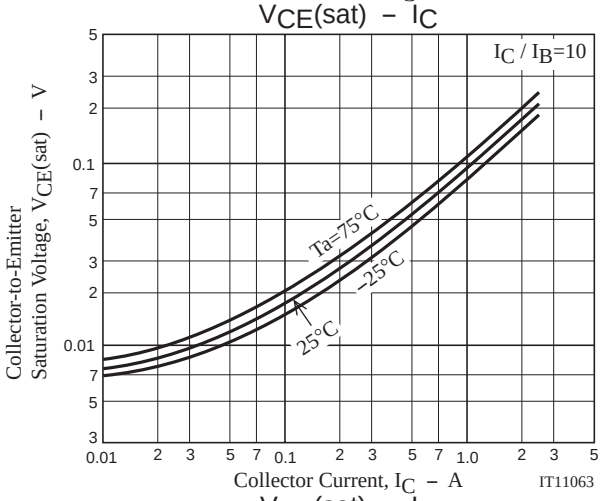

IC – VCE
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V
IT11058
40mA
60mA
80mA
100mA
20mA
10mA
5mA
2mA
1mA
IB=0mA

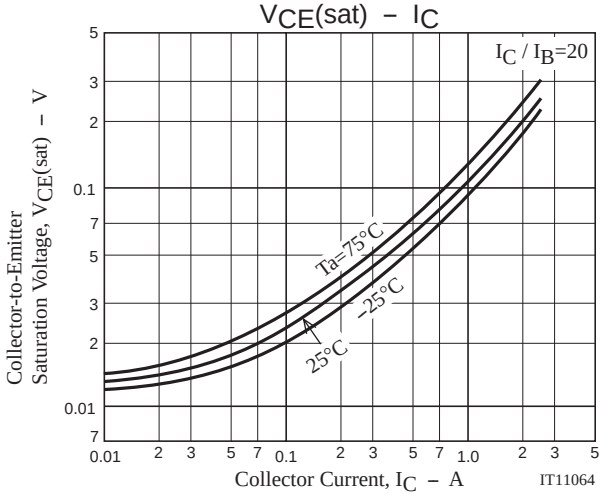

IC – VBE
Collector Current, IC – A
Base-to-Emitter Voltage, VBE – V
IT11059
VCE=5V
Ta=75°C
25°C
–25°C

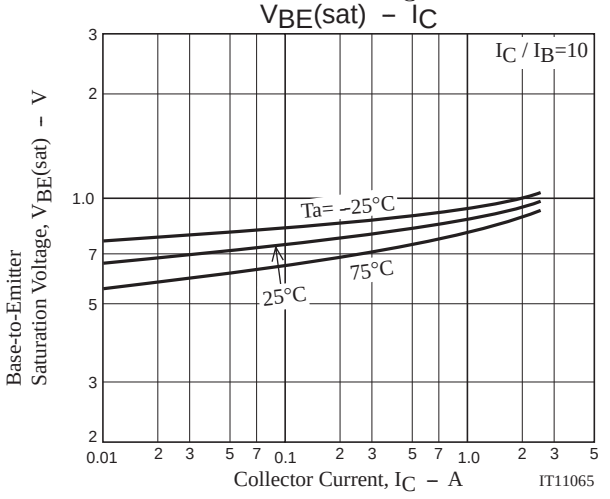

hFE – IC
DC Current Gain, hFE
Collector Current, IC – A
IT11060
VCE=5V
Ta=75°C
25°C
–25°C


fT – IC
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – A
IT11061
VCE=10V


Cob – VCB
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT11062
f=1MHz


VCE(sat) – IC
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT11063
IC / IB=10
Ta=75°C
–25°C
25°C


VCE(sat) – IC
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT11064
IC / IB=20
Ta=75°C
–25°C
25°C


VBE(sat) – IC
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
IT11065
IC / IB=10
Ta= –25°C
75°C
25°C